



PRELIMINARY

SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

Designer's Data Sheet

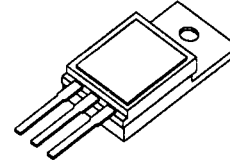
FEATURES:

- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed ceramic package
- Low inductance leads
- TX, TXV and Space Level screening available
- Replaces: IRF340 Types

SFF340C

**10 AMP
400 VOLTS
0.55Ω
N-CHANNEL
POWER MOSFET**

TO-254C



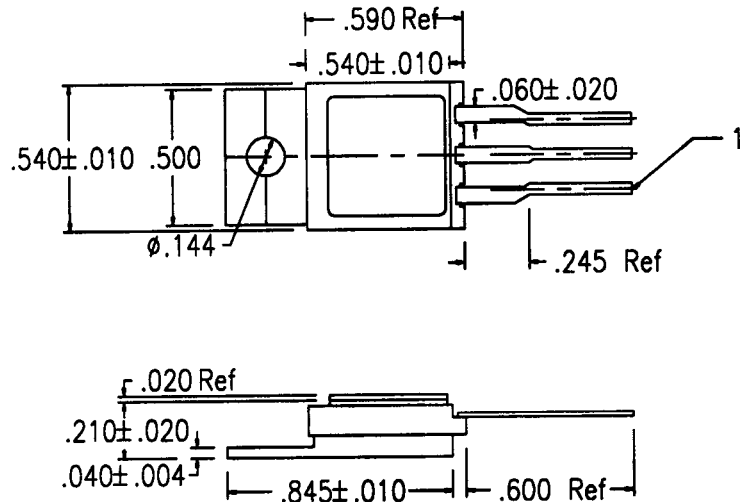
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	400	Volts
Gate to Source Voltage	V _{GS}	±20	Volts
Continuous Drain Current	I _D	10	Amps
Operating and Storage Temperature	T _{op} & T _{stg}	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	1.7	°C/W
Total Device Dissipation @ TC=25°C	P _d	76	Watts
Total Device Dissipation @ TC=55°C		55	

PACKAGE OUTLINE: CERAMIC TO-254

PIN OUT:

- PIN 1: DRAIN
- PIN 2: SOURCE
- PIN 3: GATE



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00081 A

MED

SFF340C

PRELIMINARY

SSDI**SOLID STATE DEVICES, INC**14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**ELECTRICAL CHARACTERISTICS @ T_J=25 °C (Unless Otherwise Specified)**

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (VGS=0 V, ID=250µA)		BVDSS	400	---	---	V
Drain to Source on State Resistance (VGS=10 V, ID=60% Rated ID)		RDS(on)	---	0.42	0.55	Ω
On State Drain Current (VDS > ID(on) X RDS(on) Max, VGS=10 V)		ID(on)	10	---	---	A
Gate Threshold Voltage (VDS=VGS, ID=250µA)		VGS(th)	2.0	---	4.0	V
Forward Transconductance (VDS ≥ 50V, IDS=60% rated ID)		gfs	5.8	8.7	---	S(Ω)
Zero Gate Voltage Drain Current (VDS=max rated voltage, VGS=0 V) (VDS=80% rated VDS, VGS=0 V, TA=125°C)		IDSS	---	---	250 1000	µA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated VGS	IGSS	---	---	100 -100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	VGS=10 Volts 80% rated VDS ID=10A	Qg Qgs Qgd	---	43 6 22	65 9.3 33	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	VDD=50% rated VDS ID=10A RG=9.1Ω RD=20Ω	td(on) tr td(off) tf	---	14 27 50 24	9 30 74 36	nsec
Diode Forward Voltage (IS=rated ID, VGS=0 V, T _J =25°C)		VSD	---	---	2.0	V
Diode Reverse Recovery Time Reverse Recovery Charge	T _J =25°C IF=rated ID di/dt=100 A/µsec	trr QRR	170 1.6	370 3.8	790 8.2	nsec µC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	VGS=0 Volts VDS=25 Volts f= 1 MHz	Ciss Coss Crss	---	1300 210 37	---	pF

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.